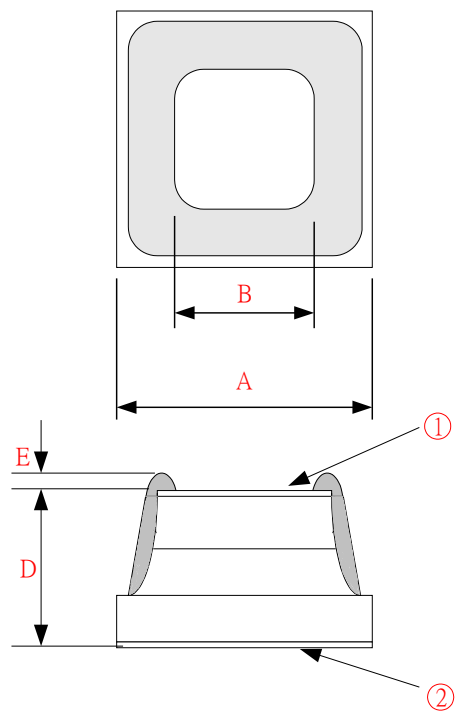


Product	Type										
Ultra Fast Rectifier Diodes Top Au ① Bottom Au ②	GPWH75610-4-01-3RD										
Metallization Dimension in mils <table border="1" data-bbox="70 473 566 782"> <thead> <tr> <th></th> <th>Dimension</th> </tr> </thead> <tbody> <tr> <td>A</td> <td>298±2</td> </tr> <tr> <td>B</td> <td>270(min.)</td> </tr> <tr> <td>D</td> <td>10.5±1</td> </tr> <tr> <td>E</td> <td>1.5.±1</td> </tr> </tbody> </table>		Dimension	A	298±2	B	270(min.)	D	10.5±1	E	1.5.±1	
	Dimension										
A	298±2										
B	270(min.)										
D	10.5±1										
E	1.5.±1										

Absolute Maximum Ratings (Ta=25°C)

PEAK REVERSE VOLTAGE VRM .. 1000 V

FORWARD SURGE CURRENT IFSM...600 A

STORAGE TEMPERATURE RANGE Tstg .. -65~150°C

Electrical Characteristics

Item	Symbol	Test Condition	Standard
FORWARD VOLTAGE(for cell type)	VF	IF=70A	1.85 V (MAX)
REVERSE CURRENT	IR	VR=1000V	10µA (MAX)
REVERSE RECOVERY TIME	TRR	RG1	90ns
BREAKDOWN VOLTAGE	BVR	IR=10µA	1020V (MIN)

Quality Yield Assurance per wafer: 70%

Ho Chien Electronics Inc.	Spec No. GPWH75610-4-01	DATE : Sep.22.2006
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